



N-Channel Enhancement Mode MOSFET

Features

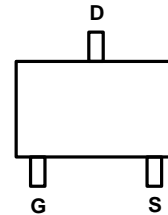
- 20V/3A,
 $R_{DS(ON)} = 50m\Omega(Typ.) @ V_{GS} = 4.5V$
 $R_{DS(ON)} = 65m\Omega(Typ.) @ V_{GS} = 2.5V$
 $R_{DS(ON)} = 120m\Omega(Typ.) @ V_{GS} = 1.8V$
- Super High Dense Cell Design
- Reliable and Rugged
- Lead Free and Green Devices Available
(RoHS Compliant)

Applications

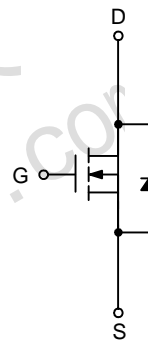
- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems

Pin Description

Top View



SOT-23



N-Channel MOSFET

Ordering and Marking Information

<p>AM2302</p> <p>Packing</p> <p>Package</p>	<p>Package R : SOT23-3L</p> <p>Packing Blank : Tube A : Taping</p>
<p>AM2302 : A2XXX XXX - Date Code</p>	

Note: AXElite lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS. AXElite lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020C for MSL classification at lead-free peak reflow temperature. AXElite defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Rating	Unit
V_{DSS}	Drain-Source Voltage		20	V
V_{GSS}	Gate-Source Voltage		± 12	
I_D^*	Continuous Drain Current	$V_{GS}=4.5V$	3	A
I_{DM}^*	300 μs Pulsed Drain Current		10	
I_S^*	Diode Continuous Forward Current		1	A
T_J	Maximum Junction Temperature		150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range		-55 to 150	
P_D^*	Maximum Power Dissipation	$T_A=25^\circ\text{C}$	0.83	W
		$T_A=100^\circ\text{C}$	0.3	
$R_{\theta JA}^*$	Thermal Resistance-Junction to Ambient		150	$^\circ\text{C}/\text{W}$

Note : *Surface Mounted on 1in² pad area, t \leq 10 Sec.

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	AM2302			Unit
			Min.	Typ.	Max.	
STATIC CHARACTERISTICS						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu\text{A}$	20	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=16V, V_{GS}=0V$ $T_J=85^\circ\text{C}$	-	-	1	μA
			-	-	30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu\text{A}$	0.5	0.7	1	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 10V, V_{DS}=0V$	-	-	± 10	μA
$R_{DS(ON)}^a$	Drain-Source On-state Resistance	$V_{GS}=4.5V, I_{DS}=3A$	-	50	65	m Ω
		$V_{GS}=2.5V, I_{DS}=2A$	-	65	90	
		$V_{GS}=1.8V, I_{DS}=0.5A$	-	120	200	
V_{SD}^a	Diode Forward Voltage	$I_{SD}=1A, V_{GS}=0V$	-	0.7	1.3	V
GATE CHARGE CHARACTERISTICS^b						
Q_g	Total Gate Charge	$V_{DS}=10V, V_{GS}=4.5V,$ $I_{DS}=3A$	-	4.4	6	nC
Q_{gs}	Gate-Source Charge		-	0.5	-	
Q_{gd}	Gate-Drain Charge		-	1.6	-	

Electrical Characteristics (Cont.) ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	AM2302			Unit
			Min.	Typ.	Max.	
DYNAMIC CHARACTERISTICS^b						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$	-	5	-	Ω
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=10V,$ Frequency=1.0MHz	-	320	-	pF
C_{oss}	Output Capacitance		-	70	-	
C_{rss}	Reverse Transfer Capacitance		-	50	-	
$t_{d(ON)}$	Turn-On Delay Time	$V_{DD}=10V, R_L=10\Omega,$ $I_{DS}=1A, V_{GEN}=4.5V,$ $R_G=6\Omega$	-	4	8	ns
t_r	Turn-On Rise Time		-	14	26	
$t_{d(OFF)}$	Turn-Off Delay Time		-	21	39	
t_f	Turn-Off Fall Time		-	5	10	
t_{rr}	Reverse Recovery Time	$I_{SD}=3A, di_{SD}/dt=100A/\mu s$	-	15	-	ns
Q_{rr}	Reverse Recovery Charge		-	6	-	nC

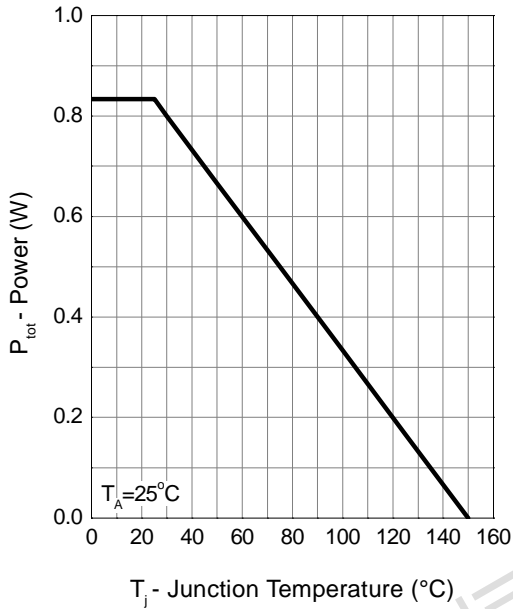
Note a : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

Note b : Guaranteed by design, not subject to production testing.

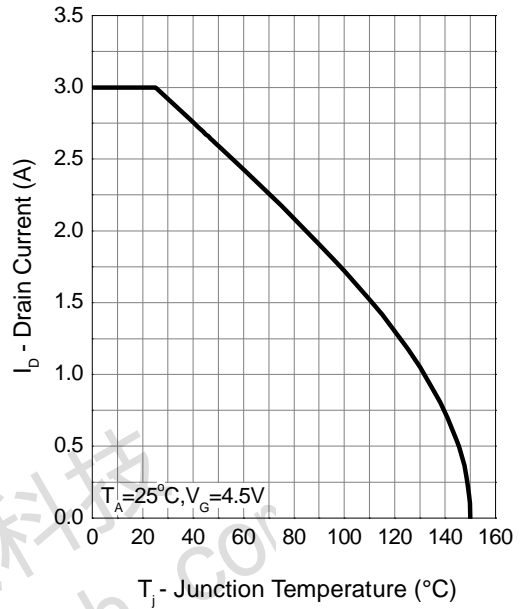
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Typical Operating Characteristics

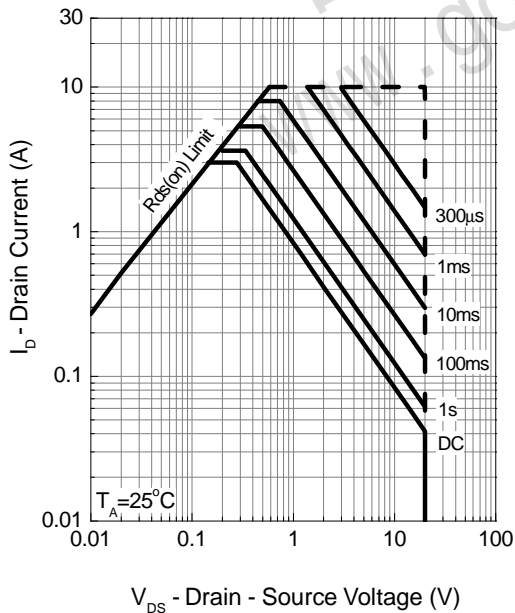
Power Dissipation



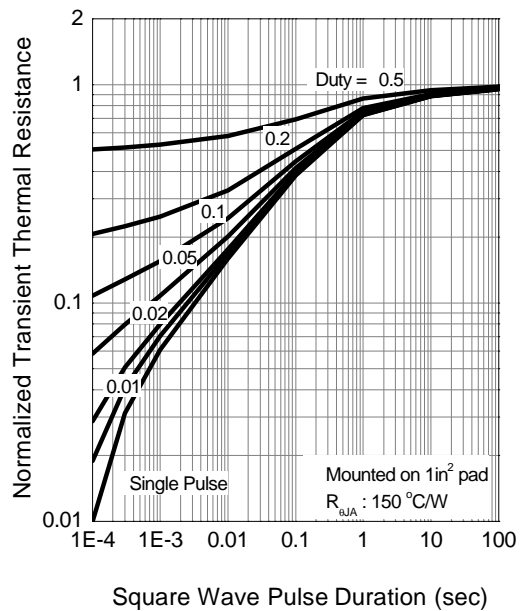
Drain Current



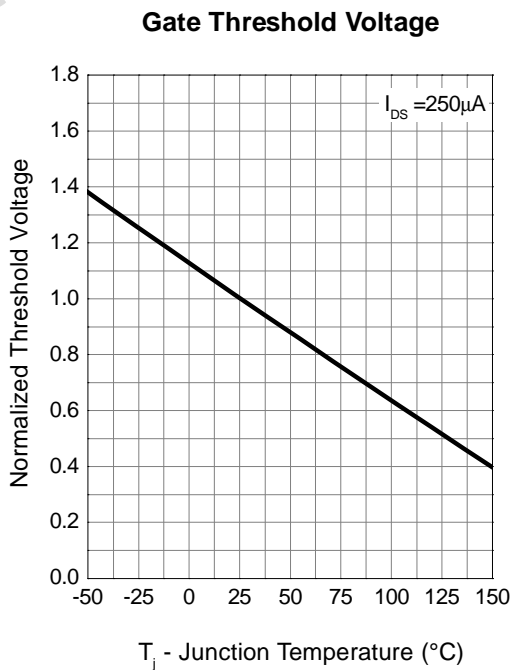
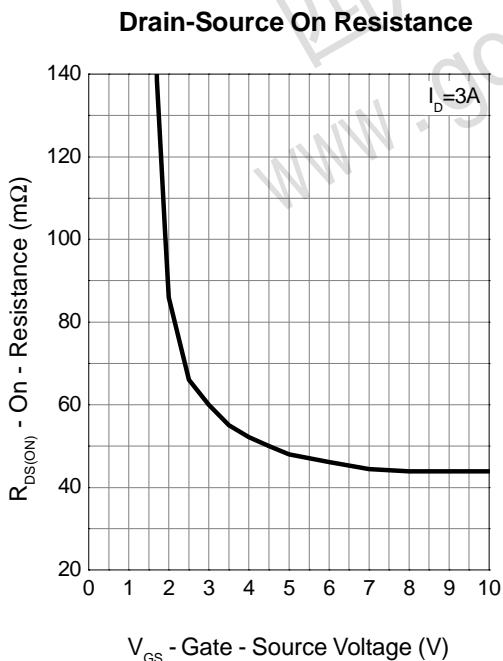
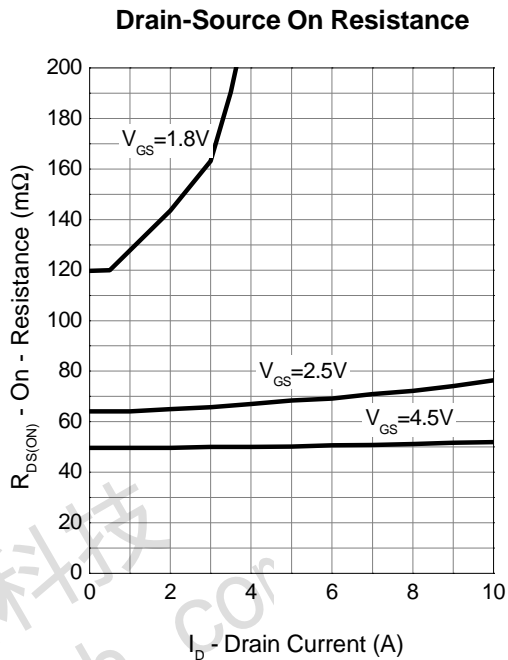
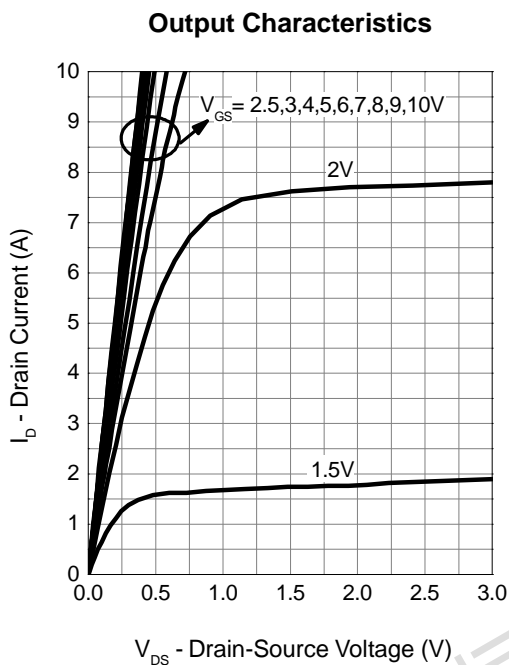
Safe Operation Area



Thermal Transient Impedance

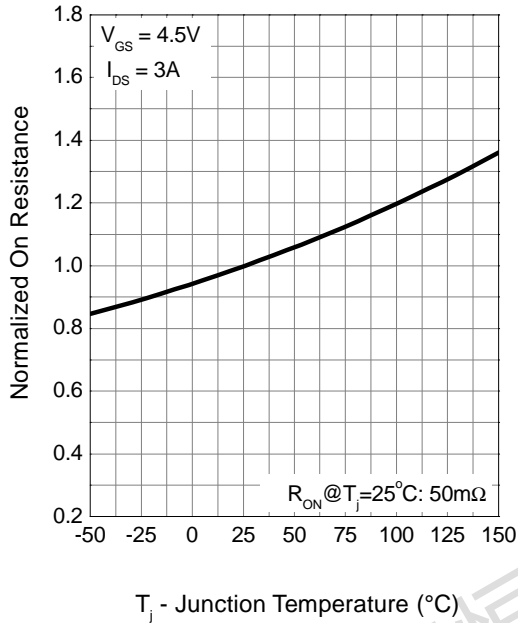


Typical Operating Characteristics (Cont.)

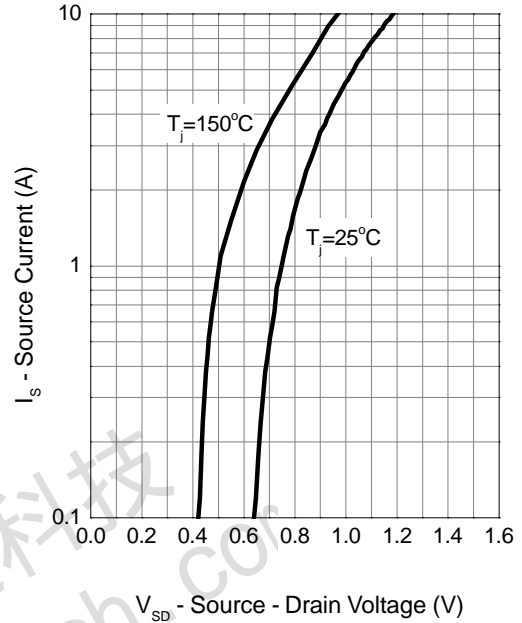


Typical Operating Characteristics (Cont.)

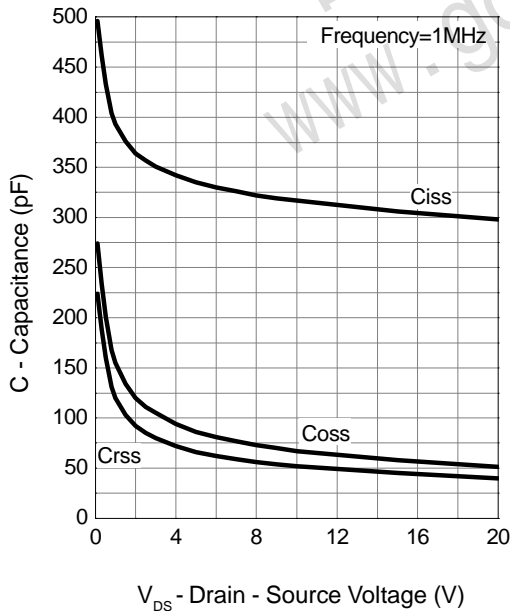
Drain-Source On Resistance



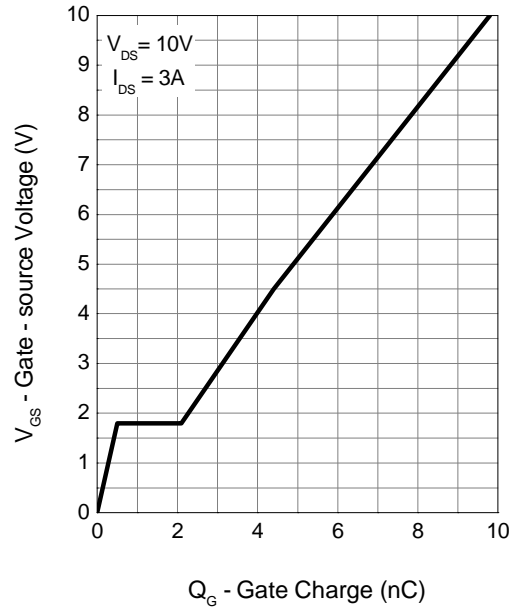
Source-Drain Diode Forward



Capacitance

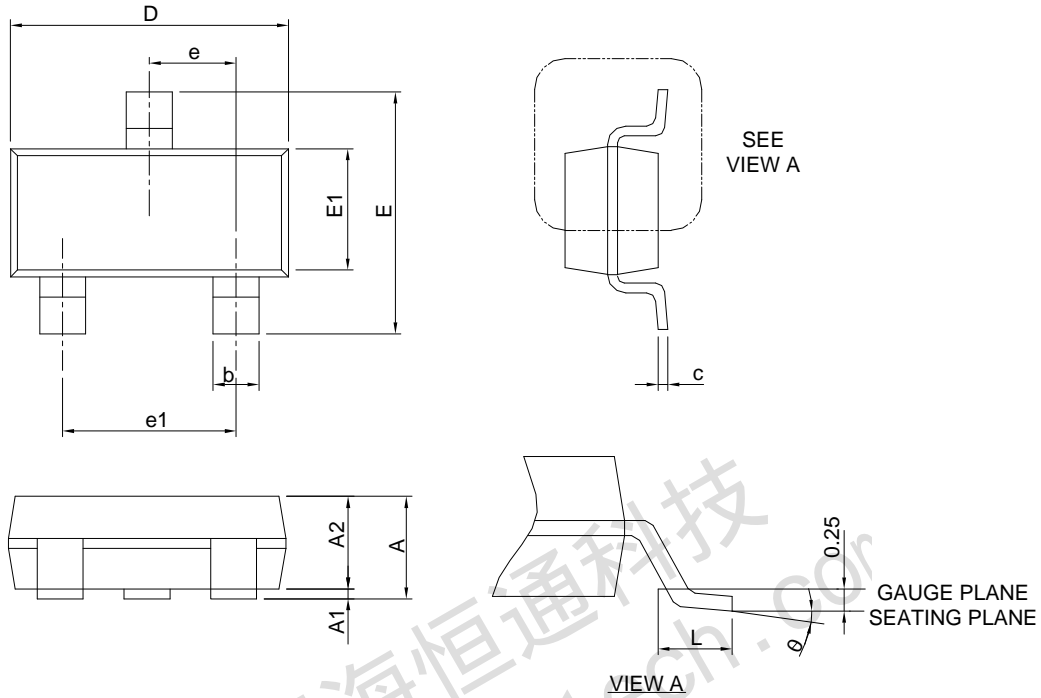


Gate Charge



Package Information

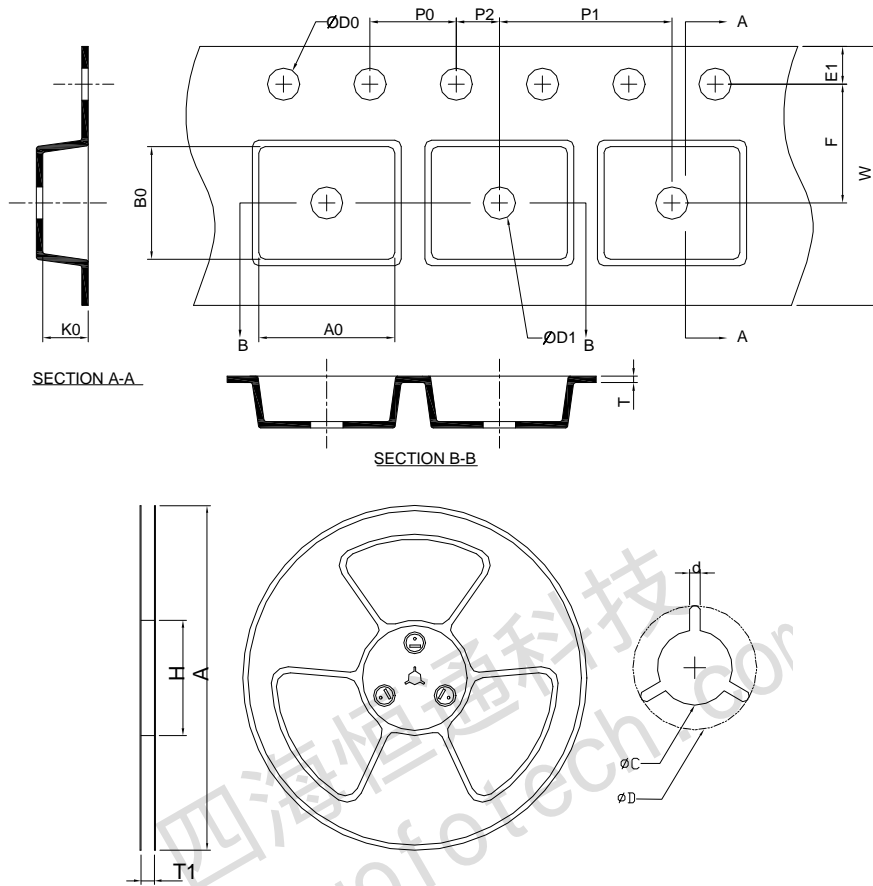
SOT-23



SYMBOL	SOT-23			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A		1.45		0.057
A1	0.00	0.15	0.000	0.006
A2	0.90	1.30	0.035	0.051
b	0.30	0.50	0.012	0.020
c	0.08	0.22	0.003	0.009
D	2.70	3.10	0.106	0.122
E	2.60	3.00	0.102	0.118
E1	1.40	1.80	0.055	0.071
e	0.95 BSC		0.037 BSC	
e1	1.90 BSC		0.075 BSC	
L	0.30	0.60	0.012	0.024
θ	0°	8°	0°	8°

Note : Dimension D and E1 do not include mold flash, protrusions or gate burrs. Mold flash, protrusion or gate burrs shall not exceed 10 mil per side.

Carrier Tape & Reel Dimensions



Application	A	H	T1	C	d	D	W	E1	F
SOT-23	178.0 ±0.00	50 MIN.	8.4+2.00 -0.00	13.0+0.50 -0.20	1.5 MIN.	20.2 MIN.	8.0 ±0.30	1.75 ±0.10	3.5 ±0.05
	P0	P1	P2	D0	D1	T	A0	B0	K0
	4.0 ±0.10	4.0 ±0.10	2.0 ±0.05	1.5+0.10 -0.00	1.0 MIN.	0.6+0.00 -0.40	3.20 ±0.20	3.10 ±0.20	1.50 ±0.20

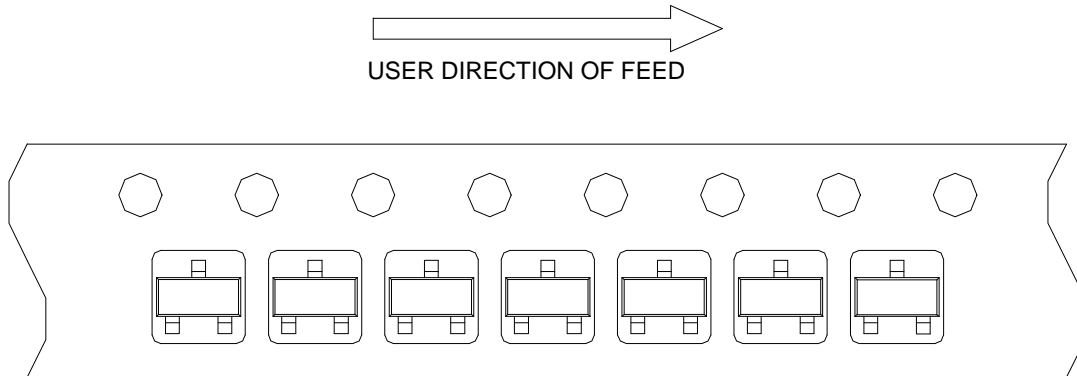
(mm)

Devices Per Unit

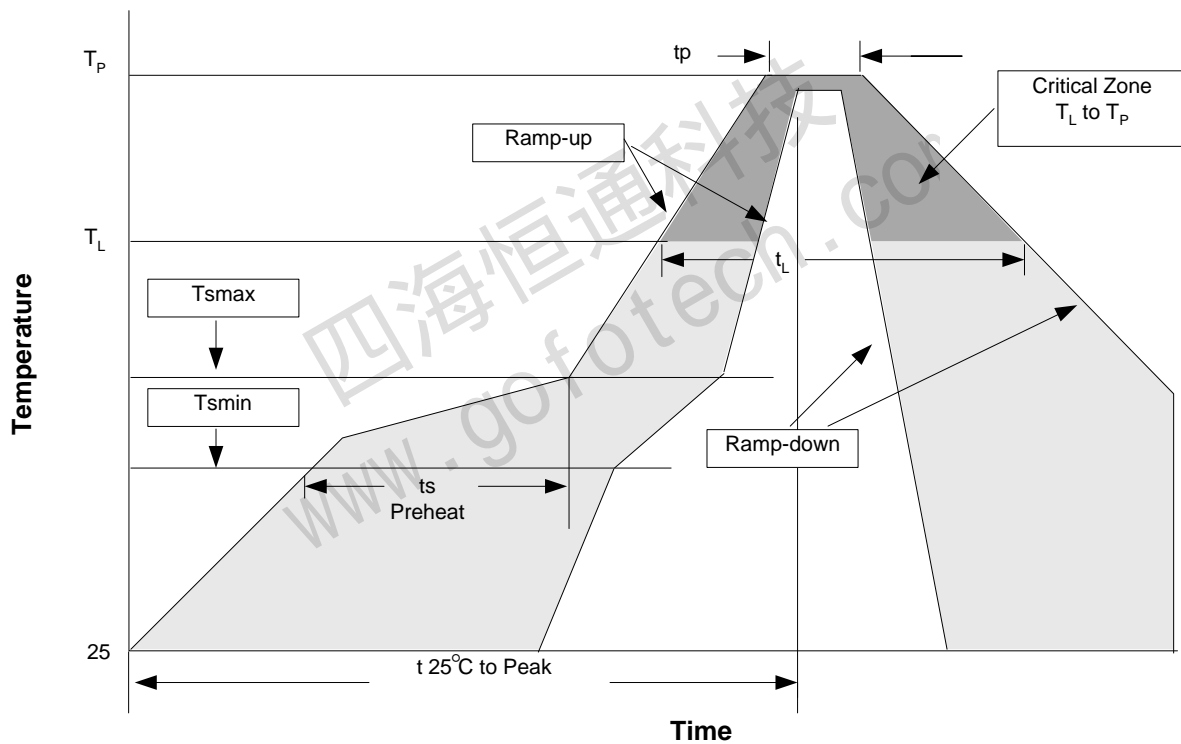
Package Type	Unit	Quantity
SOT-23	Tape & Reel	3000

Taping Direction Information

SOT-23



Reflow Condition (IR/Convection or VPR Reflow)



Reliability Test Program

Test item	Method	Description
SOLDERABILITY	MIL-STD-883D-2003	245°C, 5 SEC
HOLT	MIL-STD-883D-1005.7	1000 Hrs Bias @125°C
PCT	JESD-22-B,A102	168 Hrs, 100%RH, 121°C
TST	MIL-STD-883D-1011.9	-65°C~150°C, 200 Cycles
ESD	MIL-STD-883D-3015.7	VHBM > 2KV, VMM > 200V
Latch-Up	JESD 78	10ms, 1 _{tr} > 100mA

Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T _L to T _P)	3°C/second max.	3°C/second max.
Preheat - Temperature Min (T _{min}) - Temperature Max (T _{max}) - Time (min to max) (ts)	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
Time maintained above: - Temperature (T _L) - Time (t _L)	183°C 60-150 seconds	217°C 60-150 seconds
Peak/Classification Temperature (T _p)	See table 1	See table 2
Time within 5°C of actual Peak Temperature (t _p)	10-30 seconds	20-40 seconds
Ramp-down Rate	6°C/second max.	6°C/second max.
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.

Notes: All temperatures refer to topside of the package. Measured on the body surface.

Table 1. SnPb Eutectic Process – Package Peak Reflow Temperatures

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	240 +0/-5°C	225 +0/-5°C
≥2.5 mm	225 +0/-5°C	225 +0/-5°C

Table 2. Pb-free Process – Package Classification Reflow Temperatures

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 +0°C*	260 +0°C*	260 +0°C*
1.6 mm – 2.5 mm	260 +0°C*	250 +0°C*	245 +0°C*
≥2.5 mm	250 +0°C*	245 +0°C*	245 +0°C*

*Tolerance: The device manufacturer/supplier **shall** assure process compatibility up to and including the stated classification temperature (this means Peak reflow temperature +0°C. For example 260°C+0°C) at the rated MSL level.